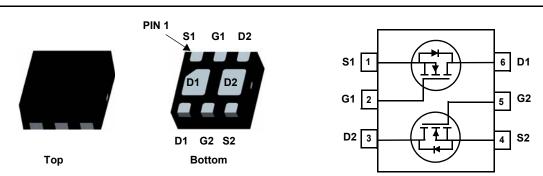


# **Dual N-Channel PowerTrench<sup>®</sup> MOSFET** 30 V, 3.8 A, 68 mΩ

### **Features**

- Max. R<sub>DS(on)</sub> = 68 mΩ at V<sub>GS</sub> = 4.5 V, I<sub>D</sub> = 3.8 A
- Max. R<sub>DS(on)</sub> = 88 mΩ at V<sub>GS</sub> = 2.5 V, I<sub>D</sub> = 3.4 A
- Max. R<sub>DS(on)</sub> = 123 mΩ at V<sub>GS</sub> = 1.8 V, I<sub>D</sub> = 2.9 A
- Low profile 0. 8 mm maximum in the new package MicroFET 2x2 mm
- RoHS Compliant





**General Description** 

suited to linear mode applications.

This device is designed specifically as a single package solution

for dual switching requirements in cellular handset and other

exceptional thermal performance for its physical size and is well

ultra-portable applications. It features two independent N-Channel MOSFETs with low on-state resistance for minimum

conduction losses. The MicroFET 2x2 package offers

**MicroFET 2x2** 

### MOSFET Maximum Ratings TA = 25 °C unless otherwise noted

Symbol	Parameter	Ratings	Units		
V <sub>DS</sub>	Drain to Source Voltage		30	V	
V <sub>GS</sub>	Gate to Source Voltage		±12	V	
ID	Drain Current -Continuous	(Note 1a)	3.8		
	-Pulsed		16	— A	
P <sub>D</sub>	Power Dissipation	(Note 1a)	1.5		
	Power Dissipation	(Note 1b)	0.7		
T <sub>J</sub> , T <sub>STG</sub>	Operating and Storage Junction Temperature Range		-55 to +150	°C	

### **Thermal Characteristics**

	Thermal Resistance for Single Operation, Junction to Ambient	(Note 1a)	86	
	Thermal Resistance for Single Operation, Junction to Ambient	(Note 1b)	173	
P	Thermal Resistance for Dual Operation, Junction to Ambient	(Note 1c)	69	°C/W
$R_{\thetaJA}$	Thermal Resistance for Dual Operation, Junction to Ambient	(Note 1d)	151	C/vv
	Thermal Resistance for Single Operation, Junction to Ambient	(Note 1e)	160	
	Thermal Resistance for Dual Operation, Junction to Ambient	(Note 1f)	133	

### Package Marking and Ordering Information

Device Marking	Device	Package	Reel Size	Tape Width	Quantity	
328	FDMA3028N	MicroFET 2X2	7 "	8 mm	3000 units	

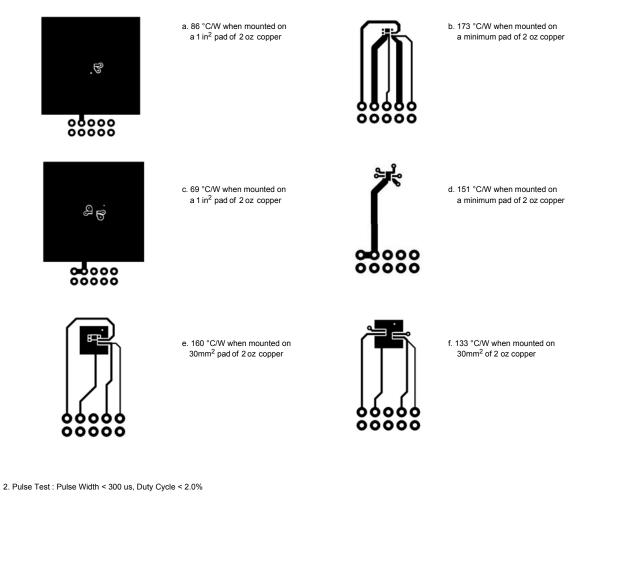
Symbol	Parameter	Test Conditions	Min	Тур	Max	Units	
Off Chara	octeristics						
BV <sub>DSS</sub>	Drain to Source Breakdown Voltage	I <sub>D</sub> = 250 μA, V <sub>GS</sub> = 0 V	30			V	
ΔBV <sub>DSS</sub> ΔT <sub>J</sub>	Breakdown Voltage Temperature Coefficient	$I_D$ = 250 µA, referenced to 25 °C		23		mV/°C	
DSS	Zero Gate Voltage Drain Current	$V_{DS}$ = 24 V, $V_{GS}$ = 0 V			1	μA	
GSS	Gate to Source Leakage Current	$V_{GS}$ = ±12 V, $V_{DS}$ = 0 V			±100	nA	
On Chara	cteristics						
V <sub>GS(th)</sub>	Gate to Source Threshold Voltage	$V_{GS} = V_{DS}, I_{D} = 250 \ \mu A$	0.6	0.9	1.5	V	
$\Delta V_{GS(th)}$ $\Delta T_J$	Gate to Source Threshold Voltage Temperature Coefficient	$I_D$ = 250 µA, referenced to 25 °C		-3		mV/°C	
r <sub>DS(on)</sub>	Static Drain to Source On Resistance	V <sub>GS</sub> = 4.5 V, I <sub>D</sub> = 3.8 A		46	68		
		V <sub>GS</sub> = 2.5 V, I <sub>D</sub> = 3.4 A		56	88	mΩ	
		V <sub>GS</sub> = 1.8 V, I <sub>D</sub> = 2.9 A		80	123		
		$V_{GS}$ = 4.5 V, I <sub>D</sub> = 3.8 A, T <sub>J</sub> = 125 °C		72	108		
9 <sub>FS</sub>	Forward Transconductance	V <sub>DS</sub> = 5 V, I <sub>D</sub> = 3.8 A		15		S	
Dynamic	Characteristics						
C <sub>iss</sub>	Input Capacitance			282	375	pF	
C <sub>oss</sub>	Output Capacitance	─ V <sub>DS</sub> = 15 V, V <sub>GS</sub> = 0 V, f = 1 MHz		40	55	pF	
C <sub>rss</sub>	Reverse Transfer Capacitance			29	45	pF	
R <sub>g</sub>	Gate Resistance			2.4		Ω	
Switching	g Characteristics						
t <sub>d(on)</sub>	Turn-On Delay			5.3	11	ns	
t <sub>r</sub>	Rise Time	V <sub>DD</sub> = 15 V, I <sub>D</sub> = 3.8 A,		3	10	ns	
d(off)	Turn-Off Delay	V <sub>GS</sub> = 4.5 V, R <sub>GEN</sub> = 6 Ω		15	27	ns	
l <sub>f</sub>	Fall Time			2.5	10	ns	
Q <sub>g(TOT)</sub>	Total Gate Charge			3.7	5.2	nC	
Q <sub>gs</sub>	Gate to Source Charge	− V <sub>DD</sub> = 15 V, I <sub>D</sub> = 3.8 A − V <sub>GS</sub> = 5 V		0.4		nC	
Q <sub>gd</sub>	Gate to Drain "Miller" Charge	VGS UV		1		nC	
	urce Diode Characteristics						
Drain-So				07	4.0	V	
	Source to Drain Diode Forward Voltage	$V_{GS} = 0 V, I_S = 1.3 A$ (Note 2)		0.7	1.2	V	
Drain-So V <sub>SD</sub> t <sub>rr</sub>	Source to Drain Diode Forward Voltage Reverse Recovery Time	$V_{GS} = 0 V, I_S = 1.3 A$ (Note 2) - $I_F = 3.8 A, di/dt = 100 A/\mu s$		0.7	1.2	ns	

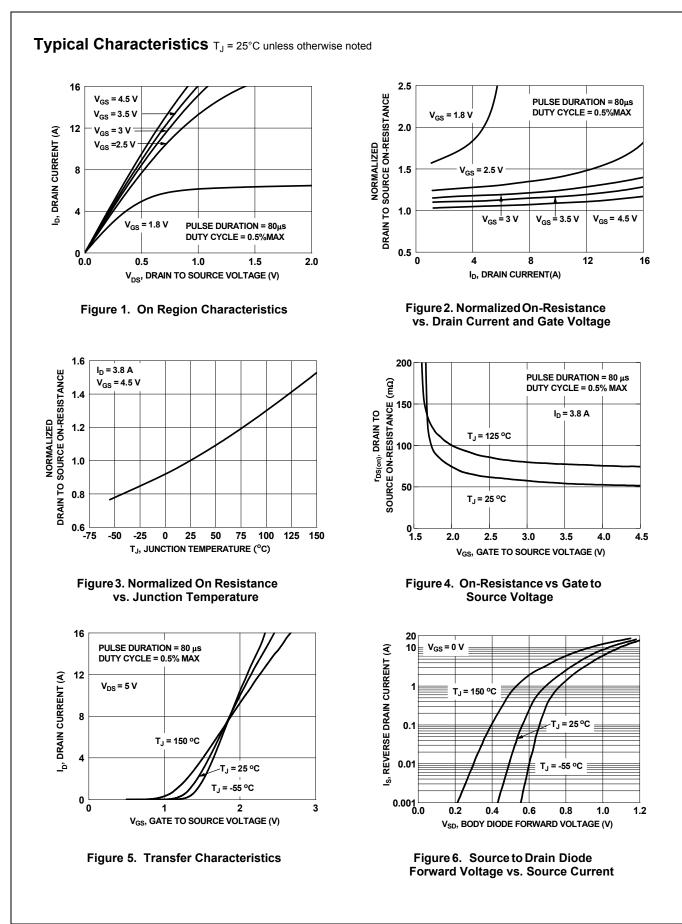
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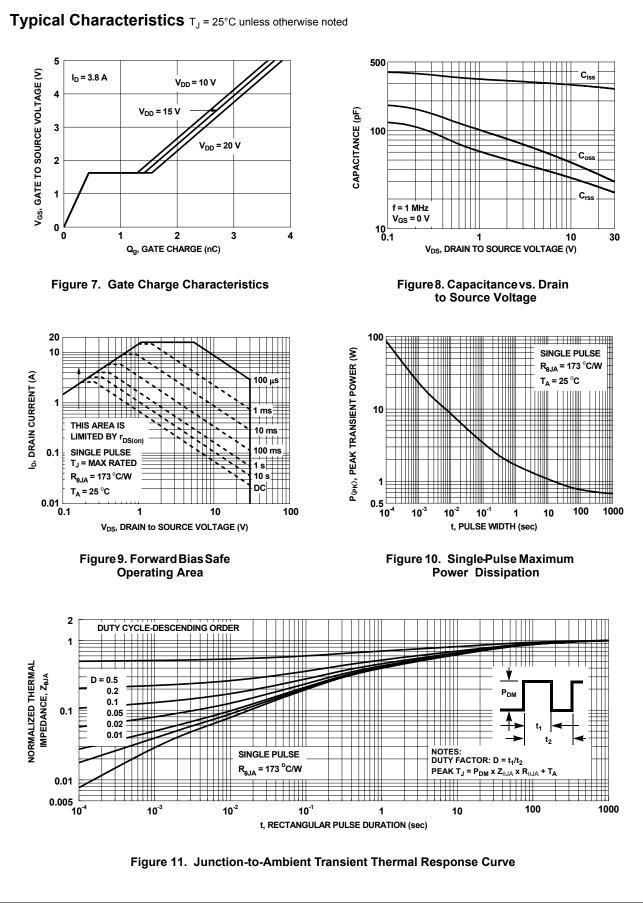
## Electrical Characteristics T<sub>J</sub> = 25 °C unless otherwise noted

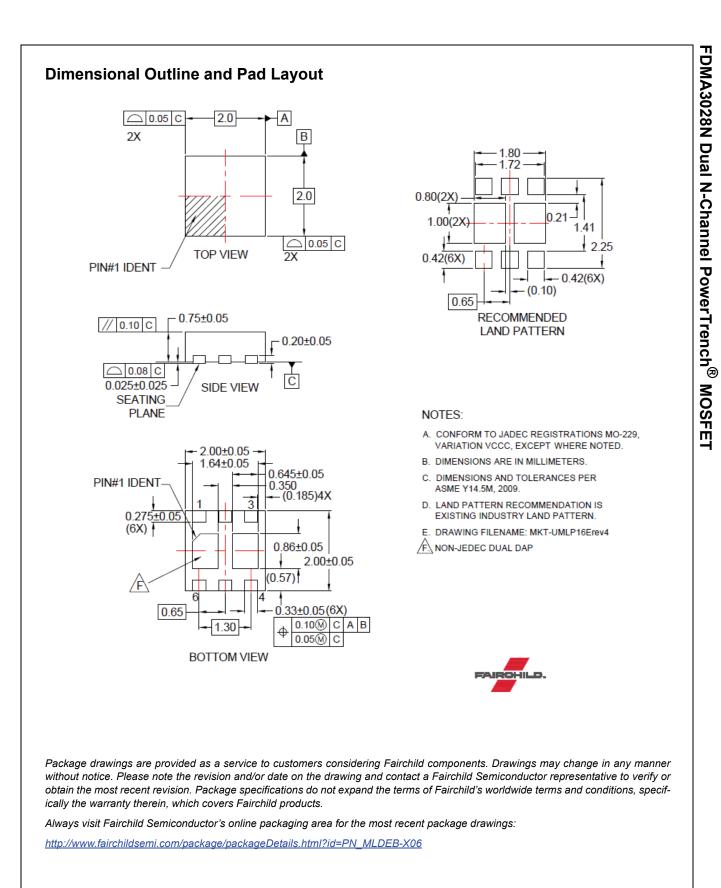
#### Notes:

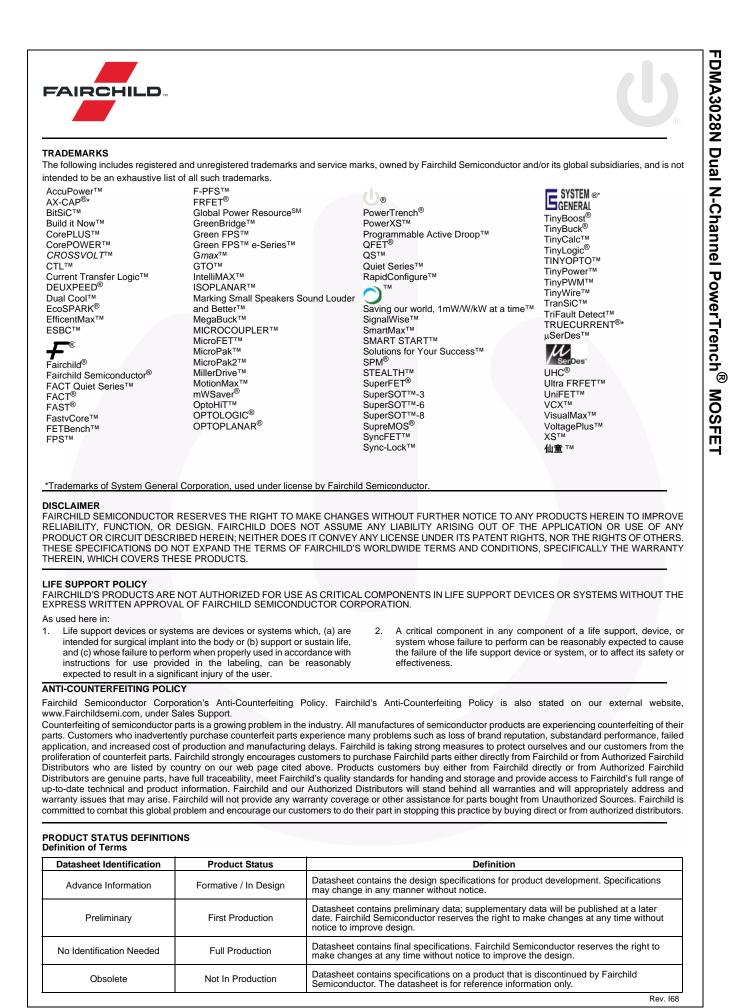
- 1. R<sub>0JA</sub> is determined with the device mounted on a 1 in<sup>2</sup> oz. copper pad on a 1.5 x 1.5 in. board of FR-4 material. R<sub>0JC</sub> is guaranteed by design while R<sub>0JA</sub> is determined by the user's board design.
- user's board design. (a)  $R_{\theta JA} = 86 \text{ °C/W}$  when mounted on a 1 in<sup>2</sup> pad of 2 oz copper, 1.5 " x 1.5 " x 0.062 " thick PCB. For single operation.
  - (b)  $R_{\theta JA}$  = 173 °C/W when mounted on a minimum pad of 2 oz copper. For single operation.
  - (c)  $R_{0JA} = 69 \text{ }^{\circ}\text{C/W}$  when mounted on a 1 in<sup>2</sup> pad of 2 oz copper, 1.5 " x 1.5 " x 0.062 " thick PCB. For dual operation.
  - (d)  $R_{\theta JA}$  = 151 °C/W when mounted on a minimum pad of 2 oz copper. For dual operation.
  - (e)  $R_{\theta JA}$  = 160 °C/W when mounted on a 30mm<sup>2</sup> pad of 2 oz copper. For single operation.
  - (f)  $R_{\theta JA}$  = 133  $^{o}\text{C/W}$  when mounted on a 30mm² pad of 2 oz copper. For dual operation.

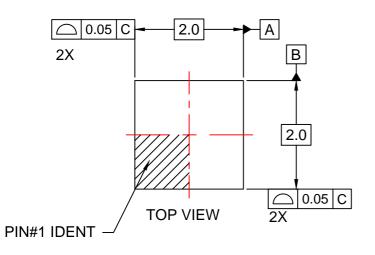


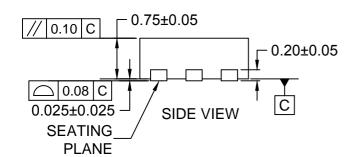


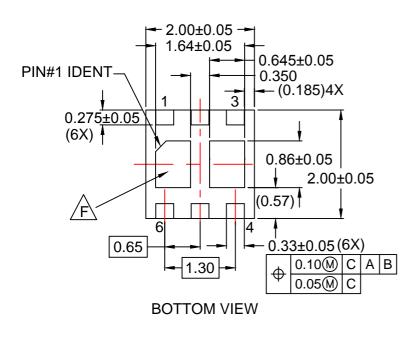


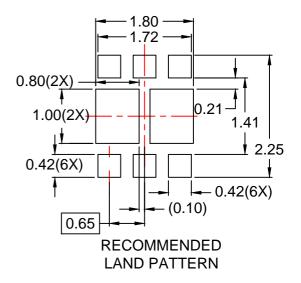












### NOTES:

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- B. DIMENSIONS ARE IN MILLIMETERS.
- C. DIMENSIONS AND TOLERANCES PER ASME Y14.5M, 2009.
- D. LAND PATTERN RECOMMENDATION IS EXISTING INDUSTRY LAND PATTERN.
- E. DRAWING FILENAME: MKT-UMLP16Erev4
- F. NON-JEDEC DUAL DAP





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